

CM1443-08CP

8-C EMI F A ESD P

Features

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- - - - -
- ± - -
- ±
-
- -
- *OptiGuard™*
- -

Applications

- R = 100 Ω
- A8) 8.5 pF 8.5 pF FILTERn* (Pins C1–C8)
- C

GND
(Pins B1–B4)

1 of 8 EMI/RFI + ESD Channels

*See Package/Pinout Diagrams for expanded pin information.

Device	Package	Shipping

s C

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PACKAGE / PINOUT DIAGRAMS

Top View
(Bumps Down View)



Bottom View
(Bumps Up View)

D

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Table 4. ELECTRICAL OPERATING CHARACTERISTICS (Note 1)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
R	Resistance		80	100	120	Ω
C_T	Total Capacitance	At 2.5 V DC	14	17	21	pF
C_S	Single Capacitor	At 2.5 V DC		8.5		pF
TCR	Temperature Coefficient of Resistance			1200		ppm/ $^{\circ}$ C
TCC	Temperature Coefficient of Capacitance	At 2.5 V DC		-300		ppm/ $^{\circ}$ C
V_{DIODE}	Diode Voltage (reverse bias)					

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PERFORMANCE INFORMATION (Cont'd)

Typical Filter Performance ($T_A = 25^\circ\text{C}$, DC Bias = 0 V, 50 Ω Environment)

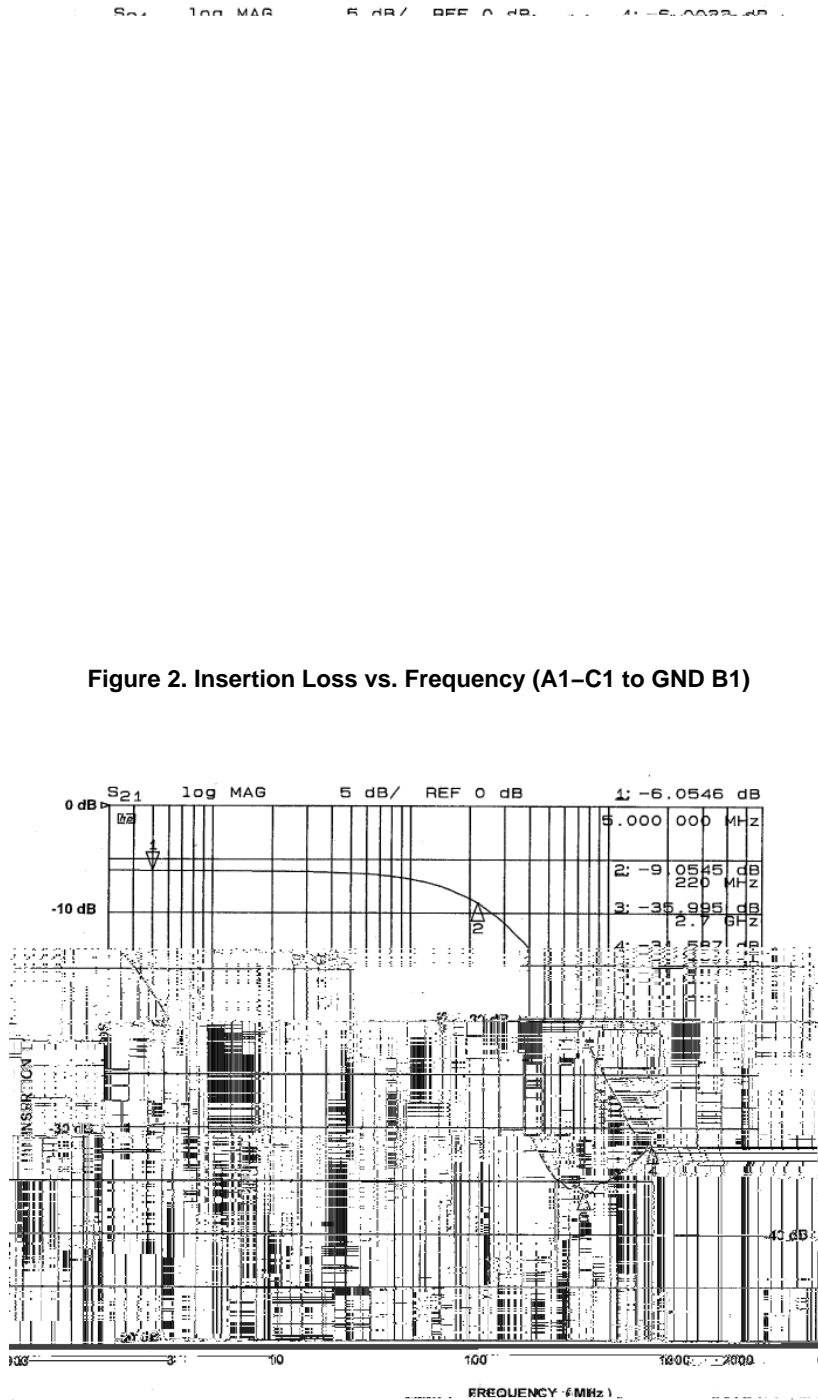


Figure 2. Insertion Loss vs. Frequency (A1-C1 to GND B1)

Figure 3. Insertion Loss vs. Frequency (A2-C2 to GND B1)

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PERFORMANCE INFORMATION (Cont'd)

Typical Filter Performance ($T_A = 25^\circ\text{C}$, DC Bias = 0 V, 50 Ω Environment)

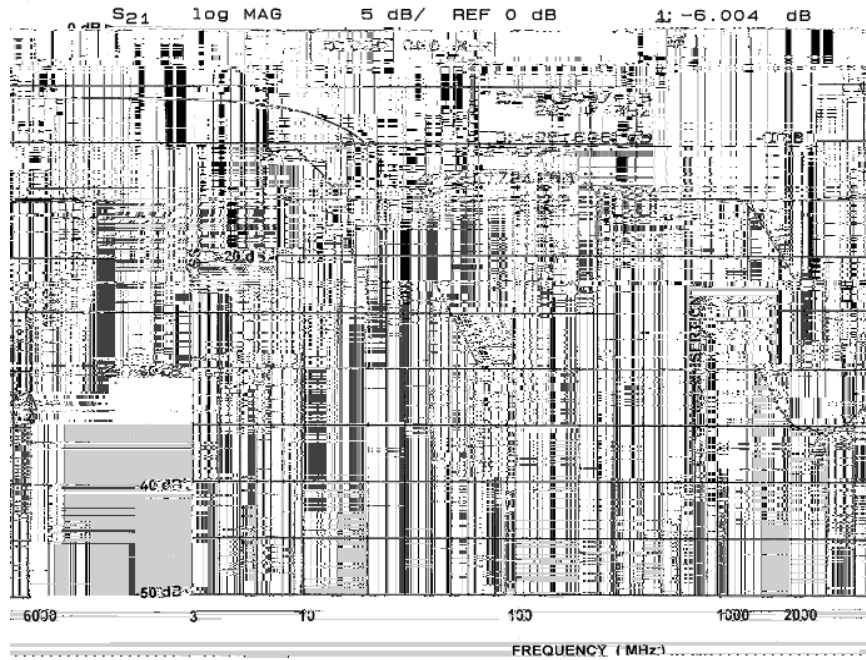


Figure 4. Insertion Loss vs. Frequency (A3-C3 to GND B2)

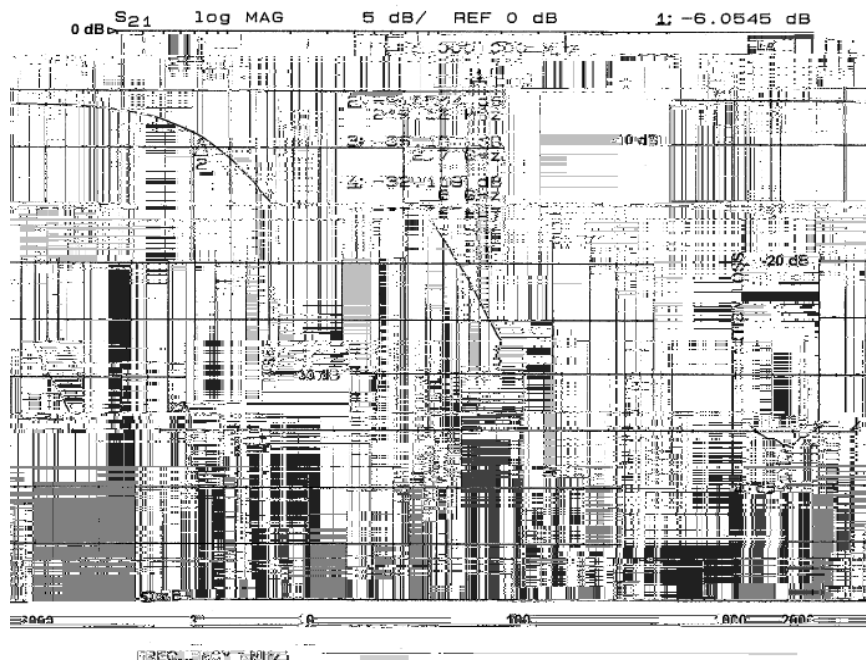


Figure 5. Insertion Loss vs. Frequency (A4-C4 to GND B2)

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PERFORMANCE INFORMATION (Cont'd)

Typical Filter Performance ($T_A = 25^\circ\text{C}$, DC Bias = 0 V, 50 Ω Environment)

S21 100 MAG 5 dB/ REF 0 dB 1: -6.0342 dB

Figure 8. Insertion Loss vs. Frequency (A7-C7 to GND B4)

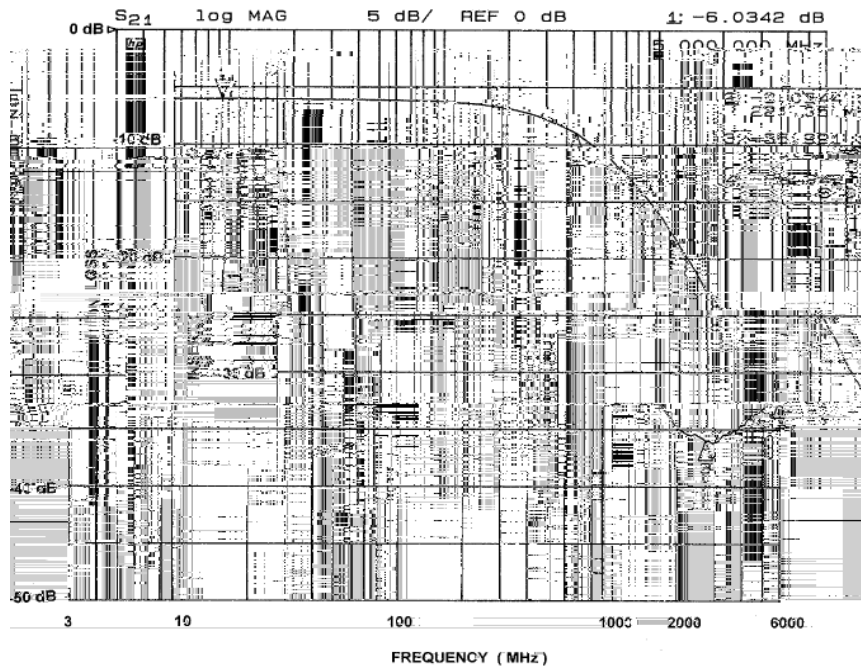


Figure 9. Insertion Loss vs. Frequency (A8-C8 to GND B4)

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PERFORMANCE INFORMATION (Cont'd)

Typical Filter Performance ($T_A = 25^\circ\text{C}$, DC Bias = 0 V, 50 Ω Environment)



Figure 10. Comparison of Filter Response Curves for CM1443 vs. DC Bias

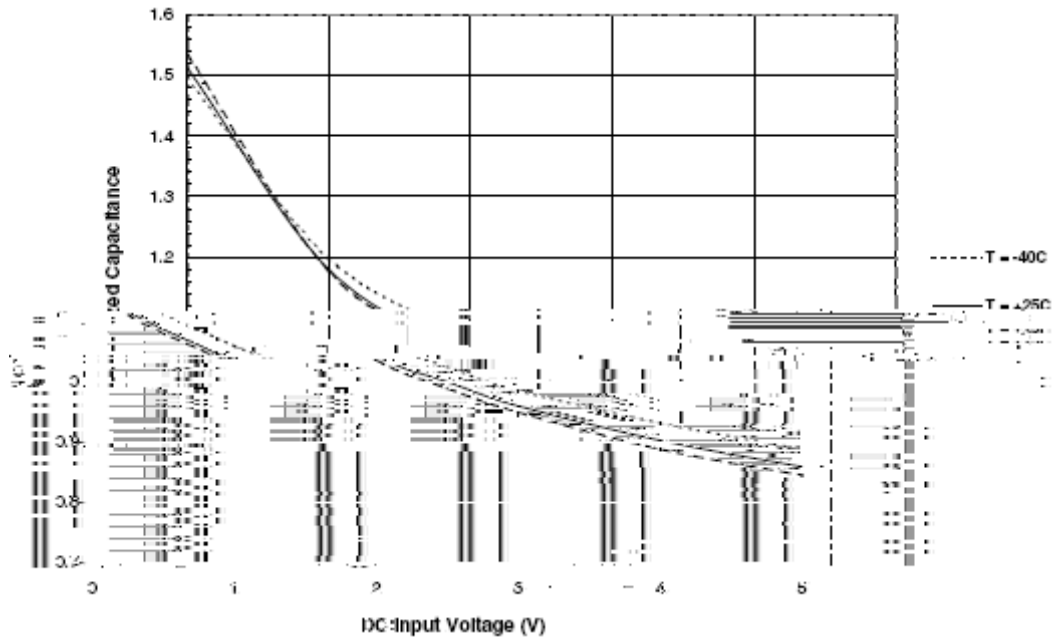
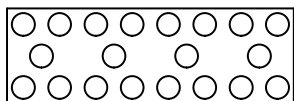


Figure 11. Filter Capacitance vs. Input Voltage over Temperature (normalized to capacitance at 2.5 VDC and 25°C)



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